

Pavel Vegeles

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48
papers

359
citations

11
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16
g-index

48
ext. papers

397
ext. citations

1.7
avg, IF

3.13
L-index

#	Paper	IF	Citations
48	Spatial variations of doping and lifetime in epitaxial laterally overgrown GaN. <i>Applied Physics Letters</i> , 2007 , 90, 152114	3.4	42
47	Donor nonuniformity in undoped and Si doped n-GaN prepared by epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , 2008 , 92, 042118	3.4	37
46	Effects of laterally overgrown n-GaN thickness on defect and deep level concentrations. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 990		36
45	Neutron Radiation Effects in Epitaxially Laterally Overgrown GaN Films. <i>Journal of Electronic Materials</i> , 2007 , 36, 1320-1325	1.9	28
44	Movement of basal plane dislocations in GaN during electron beam irradiation. <i>Applied Physics Letters</i> , 2015 , 106, 132101	3.4	19
43	EBIC and CL studies of ELOG GaN films. <i>Superlattices and Microstructures</i> , 2009 , 45, 308-313	2.8	14
42	Effect of low-energy electron irradiation on the cathodoluminescence of multiple quantum well (MQW) InGaN/GaN structures. <i>Solid State Communications</i> , 2011 , 151, 208-211	1.6	14
41	Photosensitivity of Ga ₂ O ₃ Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , 2020 , 8, 111105	5.7	13
40	EBIC characterization of light-emitting structures based on GaN. <i>Semiconductors</i> , 2007 , 41, 491-494	0.7	12
39	Recombination and optical properties of dislocations gliding at room temperature in GaN under applied stress. <i>Journal of Alloys and Compounds</i> , 2019 , 776, 181-186	5.7	12
38	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in EGa ₂ O ₃ vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 495108	3	11
37	Study of the effect of irradiation with the SEM electron beam on cathodoluminescence and the induced current in InGaN/GaN structures with multiple quantum wells. <i>Journal of Surface Investigation</i> , 2011 , 5, 945-948	0.5	9
36	Effect of low energy electron irradiation on optical properties of InGaN/GaN light emitting structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 1265-1268		9
35	Radiation enhanced basal plane dislocation glide in GaN. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FM03	1.4	9
34	Experimental estimation of electron-hole pair creation energy in EGa ₂ O ₃ . <i>Applied Physics Letters</i> , 2021 , 118, 202106	3.4	8
33	Microcathodoluminescence spectra evolution for planar and nanopillar multi-quantum-well GaN-based structures as a function of electron irradiation dose. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 011207	1.3	7
32	EBIC investigations of GaN layers prepared by epitaxial lateral overgrowth. <i>Journal of Surface Investigation</i> , 2008 , 2, 688-691	0.5	7

31	Study of dislocation EBIC image width in GaN films and GaN based structures. <i>Journal of Surface Investigation</i> , 2009 , 3, 58-60	0.5	6
30	EBIC investigation of InGaN/GaN multiple quantum well structures irradiated with low energy electrons. <i>Journal of Physics: Conference Series</i> , 2011 , 281, 012013	0.3	5
29	Electrical properties and deep traps spectra in undoped M-plane GaN films prepared by standard MOCVD and by selective lateral overgrowth. <i>Journal of Crystal Growth</i> , 2009 , 311, 2923-2925	1.6	5
28	Effect of low-energy electron irradiation on the optical properties of structures containing multiple InGaN/GaN quantum well. <i>Semiconductors</i> , 2015 , 49, 143-148	0.7	4
27	Role of extended defects in the transformation of InGaN/GaN multiple quantum well structure optical properties under low energy electron beam irradiation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 464-467		4
26	EBIC investigations of defect distribution in ELOG GaN films. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4916-4918	2.8	4
25	Investigations of electron beam induced conductivity in silicon oxide thin films. <i>Journal of Surface Investigation</i> , 2010 , 4, 754-757	0.5	4
24	Comparative study of quantum efficiency of blue LED with different nanostructural arrangement. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2981-2985		4
23	Defects with bright contrast in the induced-current mode in GaN-based light-emitting structures. <i>Journal of Surface Investigation</i> , 2007 , 1, 394-397	0.5	4
22	Estimations of Low Temperature Dislocation Mobility in GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1900163	1.6	3
21	Charging Effects in Al-SiO ₂ -p-Si Structures After Low-Energy Electron Beam Irradiation. <i>Journal of Electronic Materials</i> , 2020 , 49, 5178-5183	1.9	3
20	Dislocation gliding and cross-hatch morphology formation in AIII-BV epitaxial heterostructures. <i>Applied Physics Letters</i> , 2014 , 105, 231608	3.4	3
19	Influence of electron-beam irradiation in SEM on the cathodoluminescence and electron-beam-induced current in InGaN/GaN light-emitting diodes with a buried active region. <i>Journal of Surface Investigation</i> , 2012 , 6, 890-893	0.5	3
18	GaAs diodes for TiT-based betavoltaic cells. <i>Applied Radiation and Isotopes</i> , 2022 , 179, 110030	1.7	3
17	On the mechanism of cross-hatch pattern formation in heterostructures with a small lattice mismatch. <i>Applied Surface Science</i> , 2019 , 479, 930-941	6.7	2
16	Temperature Dependence of Low-Energy Electron Beam Irradiation Effect on Optical Properties of MQW InGaN/GaN Structures. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700646	1.3	2
15	Dislocation glide in GaN films grown by the lateral-overgrowth method induced by low-energy electron-beam irradiation. <i>Journal of Surface Investigation</i> , 2016 , 10, 959-961	0.5	2
14	Simulation and measurements of EBIC images of photoconductive elements based on HgCdTe. <i>Semiconductors</i> , 2007 , 41, 407-410	0.7	2

13	Temperature dependence of the cathodoluminescence spectra of irradiated light-emitting-diode structures with multiple InGaN/GaN quantum wells. <i>Journal of Surface Investigation</i> , 2013 , 7, 844-847	0.5	1
12	Inverse bias effect on the optical properties of light-emitting diodes with multiple InGaN/GaN quantum wells when irradiated by an electron beam in a scanning electron microscope. <i>Journal of Surface Investigation</i> , 2015 , 9, 944-947	0.5	1
11	Low energy electron beam irradiation effect on optical properties of nanopillar MQW InGaN/GaN structures 2014 ,		1
10	EBIC study of resistive photosensitive elements based on HgCdTe. <i>Semiconductors</i> , 2007 , 41, 235-239	0.7	1
9	Comparative Study of Optical and Electrical Properties of Grown-In and Freshly Introduced Dislocations in GaN by SEM Methods. <i>Journal of Electronic Materials</i> , 2020 , 49, 5173-5177	1.9	1
8	Parasitic p \bar{n} junctions formed at V-pit defects in p-GaN. <i>Journal of Applied Physics</i> , 2021 , 129, 155702	2.5	1
7	Estimations of Activation Energy for Dislocation Mobility in p-GaN. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 026004	2	1
6	Structural investigation of light-emitting A3B5 structures grown on Ge/Si(100) substrate. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 022037	0.3	1
5	Structural and optical characteristics of GaAs films grown on Si/Ge substrates. <i>Journal of Physics: Conference Series</i> , 2018 , 993, 012014	0.3	1
4	Study of Extended Electrically Active Defects in Heterostructures Based on (Ga,Mn)As/(In,Ga)As by Electron Beam-Induced Current and Deep-Level Transient Spectroscopy. <i>Journal of Surface Investigation</i> , 2019 , 13, 105-110	0.5	0
3	Communication Electron-Beam Stimulated Release of Dislocations from Pinning Sites in GaN. <i>ECS Journal of Solid State Science and Technology</i> , 2022 , 11, 015003	2	
2	Investigation of the Effect of Irradiation by a Low-Energy Electron Beam on the Capacitance-Voltage Characteristics of SiO ₂ . <i>Journal of Surface Investigation</i> , 2021 , 15, 1045-1048	0.5	
1	Investigation of the Effect of Electron-Beam Irradiation on the Defect Structure of Laterally Overgrown GaN Films via the Induced-Current and Cathodoluminescence Methods. <i>Journal of Surface Investigation</i> , 2018 , 12, 994-999	0.5	